Elektronische Bauelemente

SCP60N03S-C

60A, 30V, $R_{DS(ON)}$ 4.2mΩ

N-Channel Enhancement Mode Power MOSFET

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

SCP60N03S-C uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

FEATURES

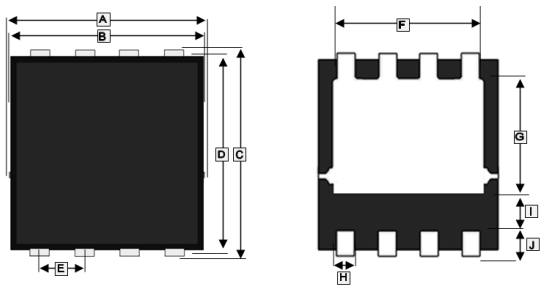
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special processing technology for high ESD capability

APPLICATIONS

- Hard Switched and High Frequency Circuits
- SMPS and general purpose applications

MARKING

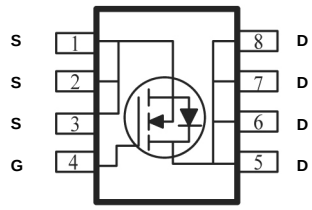
DFN3x3-8J



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	3.2	3.4	G	1.78	1.98
B	3	3.2	H	0.25	0.35
C	3.25	3.45	I	0.35 TYP.	
D	3	3.2	J	0.60 TYP.	
E	0.65 BSC.		K	0.1	0.25
F	2.39	2.59	L	0.7	0.8

PACKAGE INFORMATION

Package	MPQ	Leader Size
DFN3x3-8J	5K	13 inch



ORDER INFORMATION

Part Number	Type
SCP60N03S-C	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1]	T_C=25℃	I_D	60	A
Pulsed Drain Current		I_{DM}	240	A
Single Pulse Avalanche Energy [2]		E_{AS}	420	mJ
Power Dissipation	T_A=25℃	P_D	3	W
	T_C=25℃		34.7	
Thermal Resistance from Junction to Ambient [1]		$R_{\theta JA}$	41.67	℃/W
Thermal Resistance from Junction to Case [1]		$R_{\theta JC}$	3.6	
Lead Temperature for Soldering Purposes @1/8'' from case for 10s		T_L	260	℃
Junction and Storage Temperature Range		T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

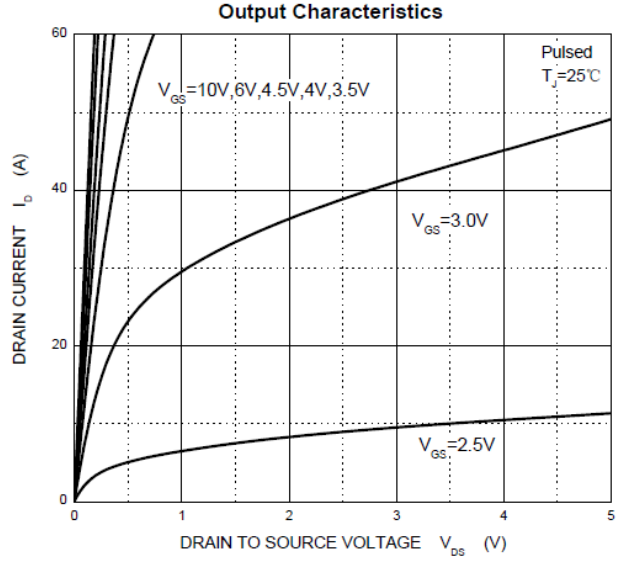
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	30	-	-	V	V_{GS}=0, I_D=250μA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	V_{DS}=24V, V_{GS}=0
Gate-Body Leakage Current	I_{GSS}	-	-	±100	nA	V_{DS}=0V, V_{GS}=±20V
Gate-Threshold Voltage	$V_{GS(th)}$	1	1.4	2.5	V	V_{DS}=V_{GS}, I_D=250μA
Static Drain-Source On-Resistance [3]	$R_{DS(ON)}$	-	3.1	4.2	mΩ	V_{GS}=10V, I_D=20A
		-	4.5	7.3		V_{GS}=4.5V, I_D=20A
Forward Transconductance	g_{fs}	-	24	-	S	V_{DS}=10V, I_D=20A
Total Gate Charge	Q_g	-	54	-	nC	V_{DS}=25V V_{GS}=10V I_D=14A
Gate-Source Charge	Q_{gs}	-	4.1	-		
Gate-Drain Charge	Q_{gd}	-	19	-		
Turn-on Delay Time	$T_{d(on)}$	-	19	-	nS	V_{DD}=15V V_{GS}=10V R_G=3Ω R_L=0.75Ω
Rise Time	T_r	-	44	-		
Turn-off Delay Time	$T_{d(off)}$	-	58	-		
Fall Time	T_f	-	16.7	-		
Input Capacitance	C_{iss}	-	2412	-	pF	V_{DS}=15V V_{GS}=0 f=1MHz
Output Capacitance	C_{oss}	-	420	-		
Reverse Transfer Capacitance	C_{rss}	-	396	-		
Drain-Source Diode						
Diode Forward Voltage [3]	V_{SD}	-	-	1.2	V	V_{GS}=0, I_S=12A
Continuous Source Current [1]	I_S	-	-	60	A	
Pulsed Source Current	I_{SM}	-	-	240	A	

Notes:

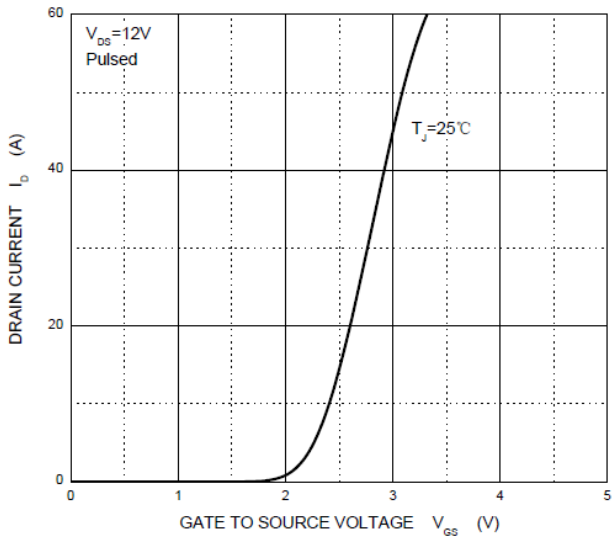
1. Mounted on a 25.4mm × 25.4mm × 0.8mm glass epoxy board.
2. Test condition: V_{DD}=15V, L=0.1mH, R_G=25Ω, Starting T_J=25℃.
3. Pulse Test: Pulse width≦300uS, duty cycle≦2%.

CHARACTERISTICS CURVE

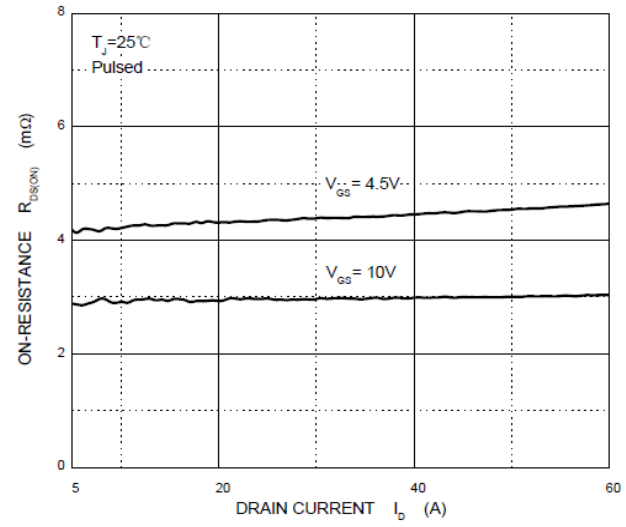
Output Characteristics



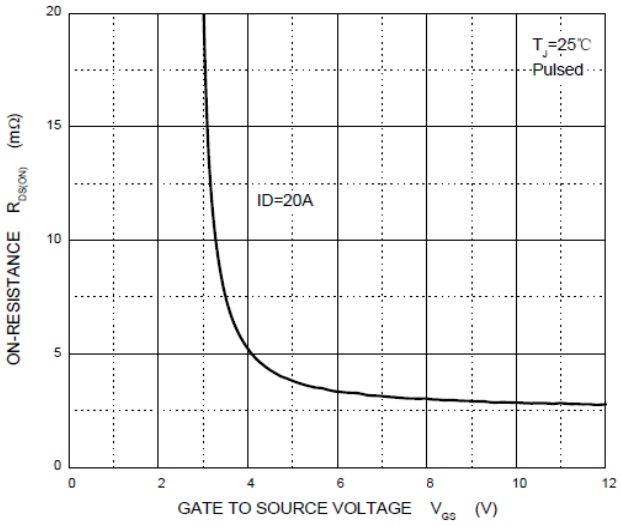
Transfer Characteristics



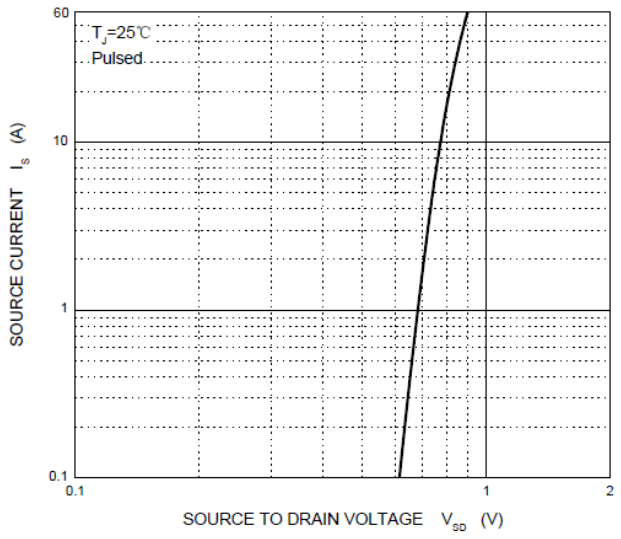
$R_{DS(ON)}$ —— I_D



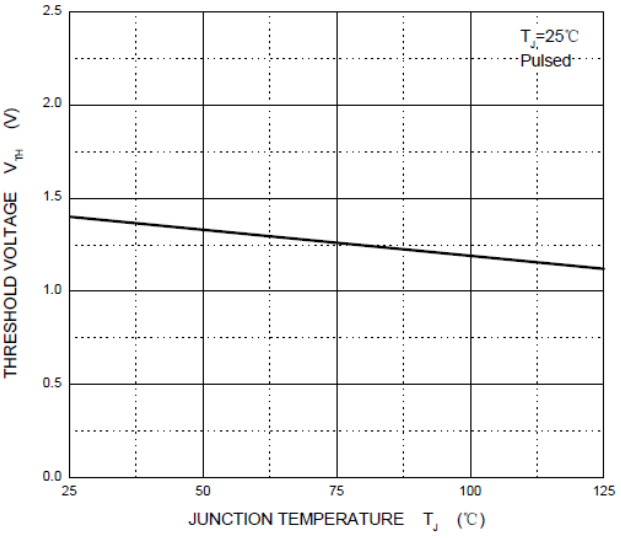
$R_{DS(ON)}$—— V_{GS}



I_S —— V_{SD}

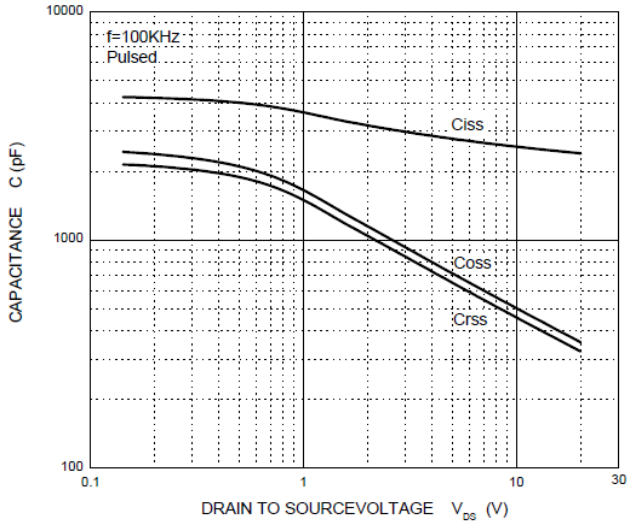


Threshold Voltage

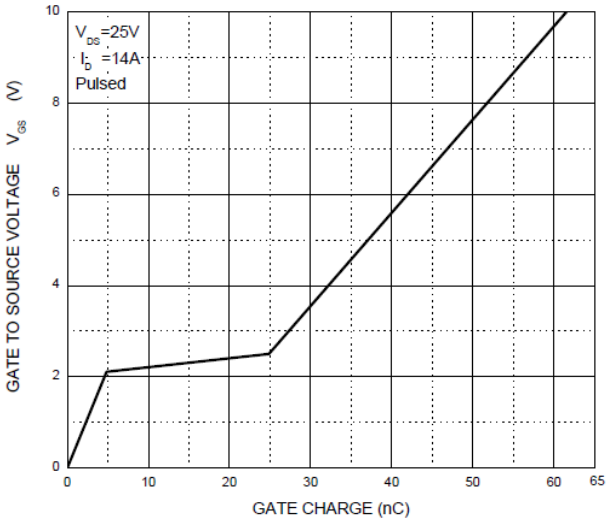


CHARACTERISTICS CURVE

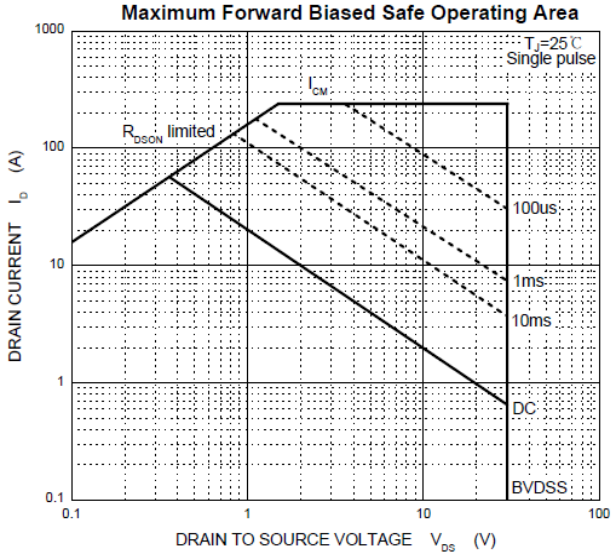
Capacitances



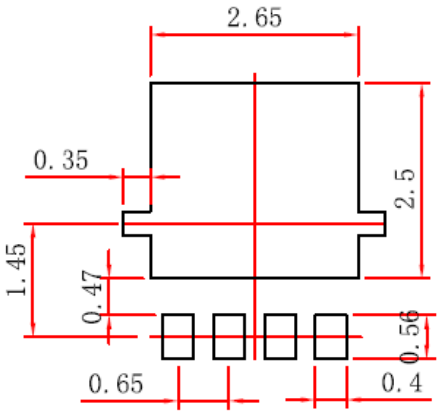
Gate Charge



Maximum Forward Biased Safe Operating Area



Mounting Pad Layout



*Dimensions in millimeters